

Title (en)

A CAPLESS ANNEALING METHOD FOR ION-IMPLANTED III-V COMPOUNDS

Publication

EP 0038915 B1 19840509 (EN)

Application

EP 81101363 A 19810225

Priority

US 14291680 A 19800423

Abstract (en)

[origin: EP0038915A1] Thermal decomposition is reduced and stoichiometry retained during annealing of a multiple element intermetallic semiconductor material by heating it in an environment with an excess of the most volatile constituent, in particular, when annealing a Si implanted GaAs wafer (58) while in proximity to InAs (50).

IPC 1-7

H01L 21/324

IPC 8 full level

H01L 21/265 (2006.01); **H01L 21/324** (2006.01)

CPC (source: EP US)

H01L 21/3245 (2013.01 - EP US); **Y10S 148/056** (2013.01 - EP US); **Y10S 148/084** (2013.01 - EP US)

Cited by

EP0226311A3; DE19633183A1; EP0111085A3

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

EP 0038915 A1 19811104; **EP 0038915 B1 19840509**; CA 1180256 A 19850102; DE 3163454 D1 19840614; JP S56158433 A 19811207; JP S586300 B2 19830203; US 4312681 A 19820126

DOCDB simple family (application)

EP 81101363 A 19810225; CA 371106 A 19810217; DE 3163454 T 19810225; JP 3807281 A 19810318; US 14291680 A 19800423